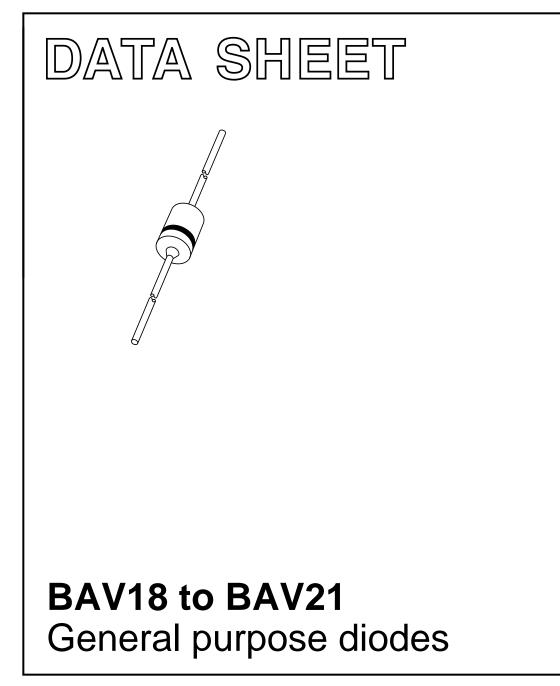
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of April 1992 File under Discrete Semiconductors, SC01 1996 Apr 19



BAV18 to BAV21

FEATURES

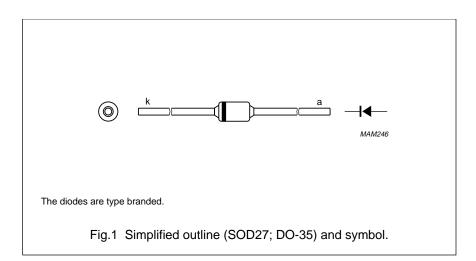
- Hermetically sealed leaded glass SOD27 (DO-35) package
- Switching speed: max. 50 ns
- General application
- Continuous reverse voltage: max. 50 V, 100 V, 150 V, 200 V
- Repetitive peak reverse voltage: max. 60 V, 120 V, 200 V, 250 V
- Repetitive peak forward current: max. 625 mA
- Forward voltage: max.1 V.

APPLICATIONS

 General purposes in industrial equipment e.g. oscilloscopes, digital voltmeters and video output stages in colour television.

DESCRIPTION

The BAV18, BAV19, BAV20, BAV21 are switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD27 (DO-35) packages.



BAV18 to BAV21

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage				
	BAV18		_	60	V
	BAV19		_	120	V
	BAV20		_	200	V
	BAV21		_	250	V
V _R	continuous peak reverse voltage				
	BAV18		_	50	V
	BAV19		_	100	V
	BAV20		_	150	V
	BAV21		_	200	V
IF	continuous forward current	see Fig.2; note 1	_	250	mA
I _{FRM}	repetitive peak forward current		_	625	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	9	A
		t = 100 μs	_	3	A
		t = 1 s	_	1	A
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	400	mW
T _{stg}	storage temperature		-65	+175	°C
Tj	junction temperature		_	175	°C

Note

1. Device mounted on an FR4 printed circuit-board; lead length 10 mm.

BAV18 to BAV21

ELECTRICAL CHARACTERISTICS

 T_j = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _F	forward voltage	see Fig.3			
		I _F = 100 mA	_	1.0	V
		I _F = 200 mA	-	1.25	V
I _R	reverse current	see Fig.5			
		$V_{R} = V_{Rmax}$	-	100	nA
		$V_R = V_{Rmax}$; $T_j = 150 \ ^\circ C$	-	100	μA
C _d	diode capacitance	$f = 1 MHz; V_R = 0; see Fig.6$	-	5	pF
t _{rr}	reverse recovery time	when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100 \Omega$; measured at $I_R = 3$ mA; see Fig.8	_	50	ns

THERMAL CHARACTERISTICS

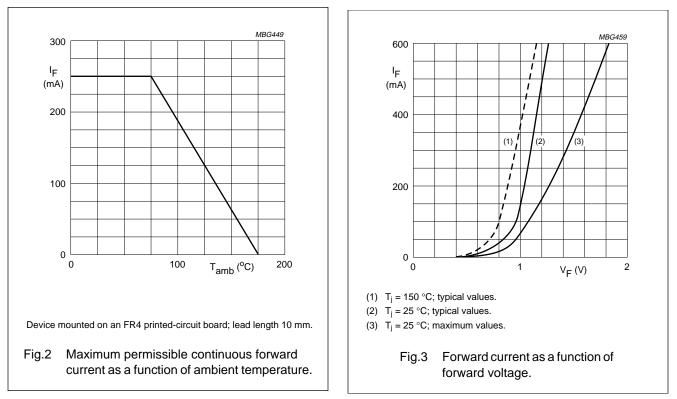
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	lead length 10 mm	240	K/W
R _{th j-a}	thermal resistance from junction to ambient	lead length 10 mm; note 1	375	K/W

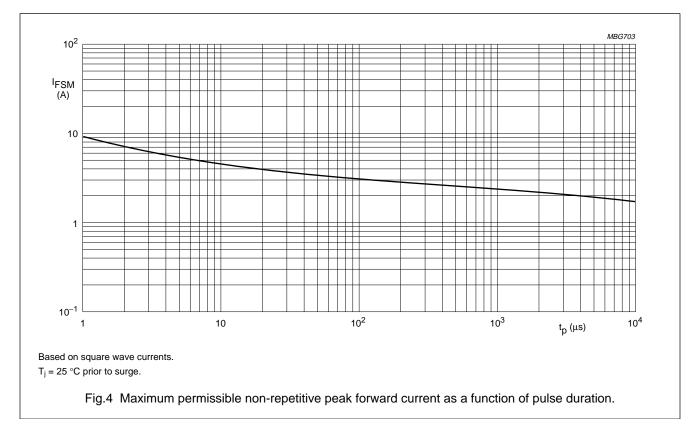
Note

1. Device mounted on a printed circuit-board without metallization pad.

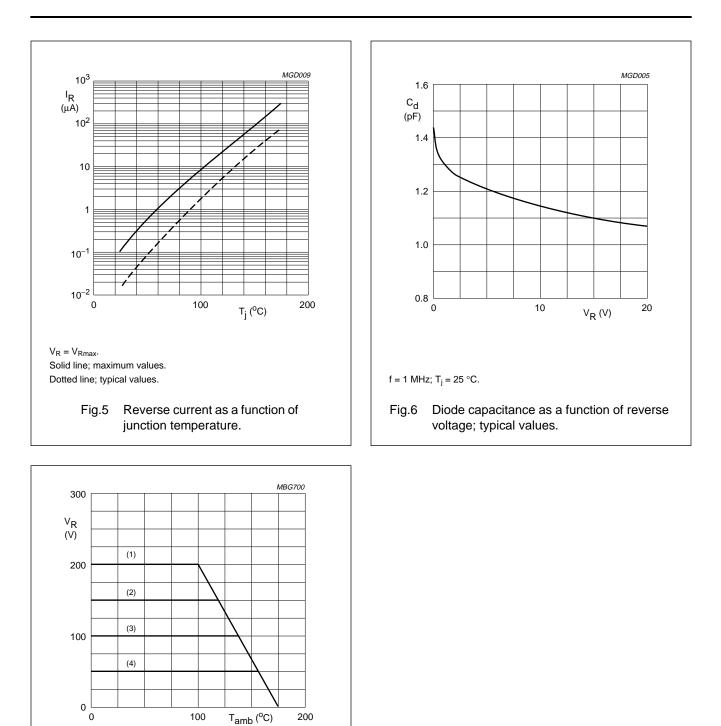
BAV18 to BAV21

GRAPHICAL DATA



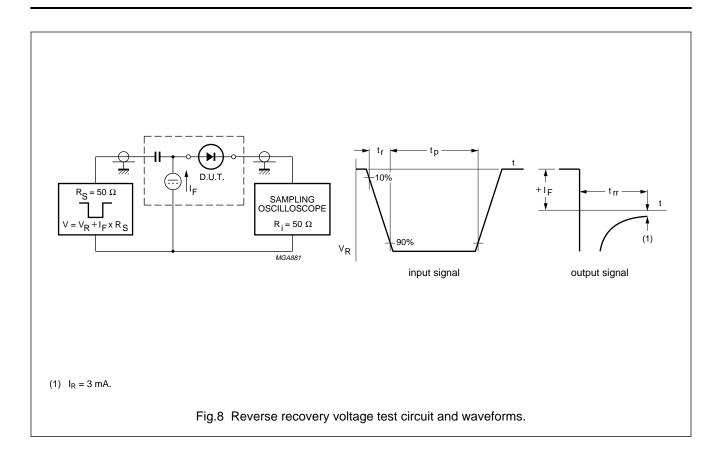


BAV18 to BAV21



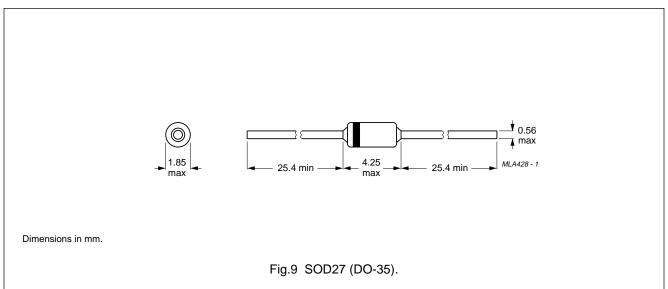
- (1) BAV21.(2) BAV20.
- (3) BAV19.
- (4) BAV18.
- Fig.7 Maximum permissible continuous reverse voltage as a function of ambient temperature.

BAV18 to BAV21



BAV18 to BAV21

PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status		
Objective specification	ective specification This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification	This data sheet contains final product specifications.	
Limiting values		
more of the limiting values of the device at these or at	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or may cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification limiting values for extended periods may affect device reliability.	
Application information		

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.